

● General Description

The AGM18N10AP combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

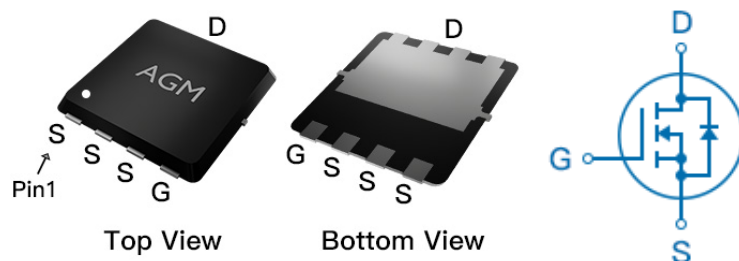
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
100V	17mΩ	35A

PDFN3.3*3.3 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM18N10AP	AGM18N10AP	PDFN3.3*3.3	330mm	12mm	5000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	100	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	35	A
	Drain Current-Continuous(Tc=100°C)	21	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	140	A
PD	Maximum Power Dissipation(Tc=25°C)	45	w
	Maximum Power Dissipation(Tc=100°C)	18	w
EAS	Avalanche energy (Note 3)	64	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	--	65	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	2.78	°C/W

Table 3. Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	100	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=100V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	1.6	2.2	V
gFS	Forward Transconductance	VDS=5V,ID=8A	--	13	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=12A	--	17	21	mΩ
		VGS=4.5V, ID=8A	--	20	26	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=50V,VGS=0V, F=1MHZ	--	573	--	pF
Coss	Output Capacitance		--	166	--	pF
Crss	Reverse Transfer Capacitance		--	5.3	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	4.5	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=50V, ID=10A, RGEN=4Ω	--	13	--	nS
tr	Turn-on Rise Time		--	16	--	nS
td(off)	Turn-Off Delay Time		--	23	--	nS
tf	Turn-Off Fall Time		--	6	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=50V, ID=10A	--	12.5	--	nC
Qgs	Gate-Source Charge		--	1.9	--	nC
Qgd	Gate-Drain Charge		--	3.0	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	35	A
VSD	Forward on Voltage	VGS=0V,IS=12A	--	--	1.2	V
trr	Reverse Recovery Time	IF=12A , dI/dt=100A/μs , TJ=25°C	--	43	--	ns
Qrr	Reverse Recovery Charge		--	87	--	nc

Notes 1.The maximum current rating is package limited.

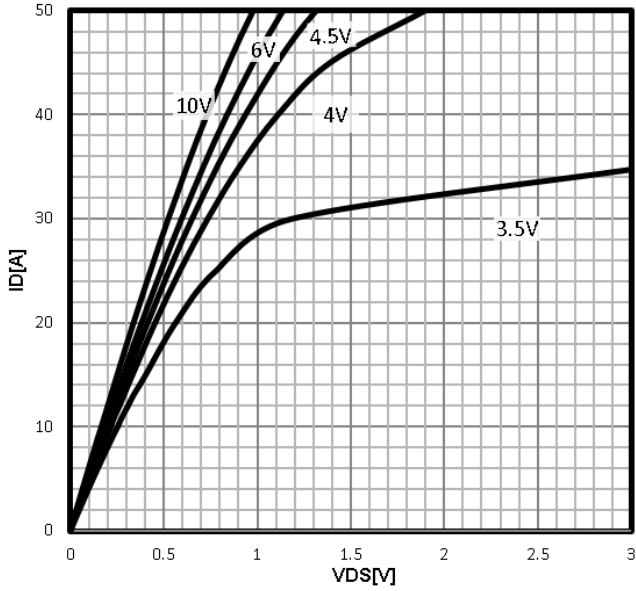
Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T_J=25°C,VDD=50V,Vgs=10V , ID=16A,L=0.5mH,RG=25ohm

Characteristics Curve:

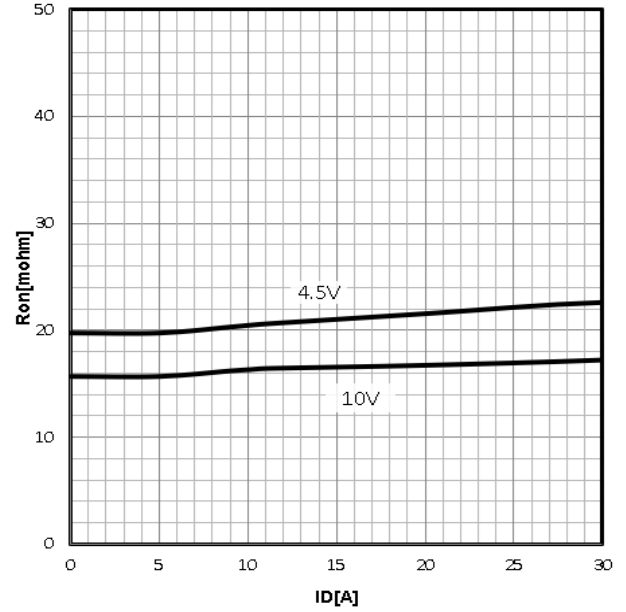
Typ. output characteristics

$$I_D = f(V_{DS})$$



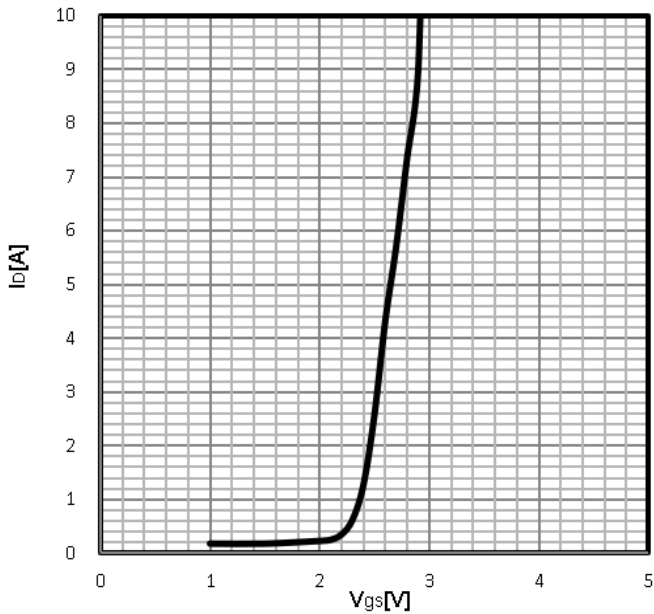
Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$



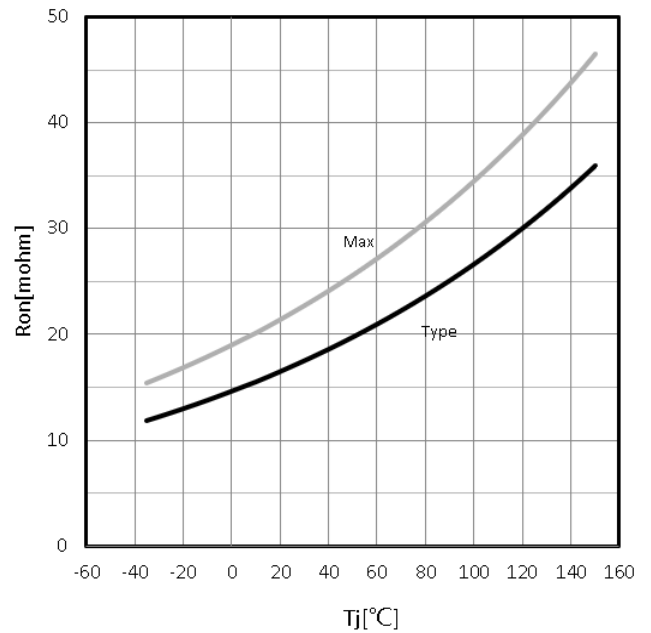
Typ. transfer characteristics

$$I_D = f(V_{GS})$$



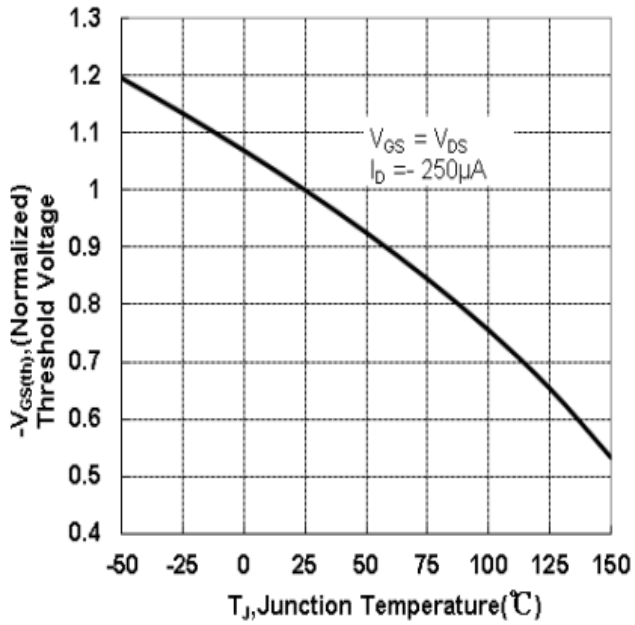
Drain-source on-state resistance

$$R_{DS(on)} = f(T_j); I_D = 10A; V_{GS} = 10V$$

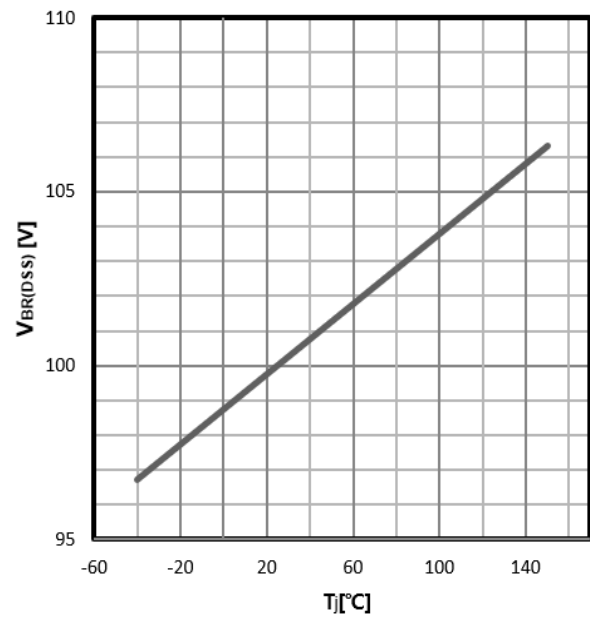


Gate Threshold Voltage

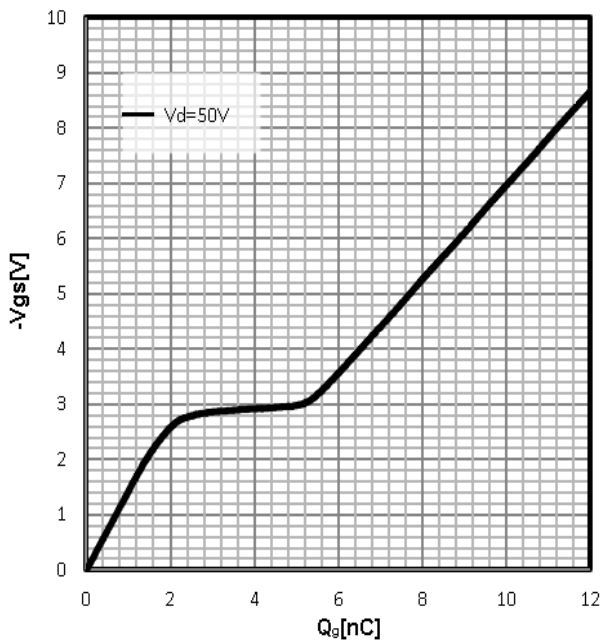
$$V_{TH}=f(T_j); I_D=250\mu A$$


Drain-source breakdown voltage

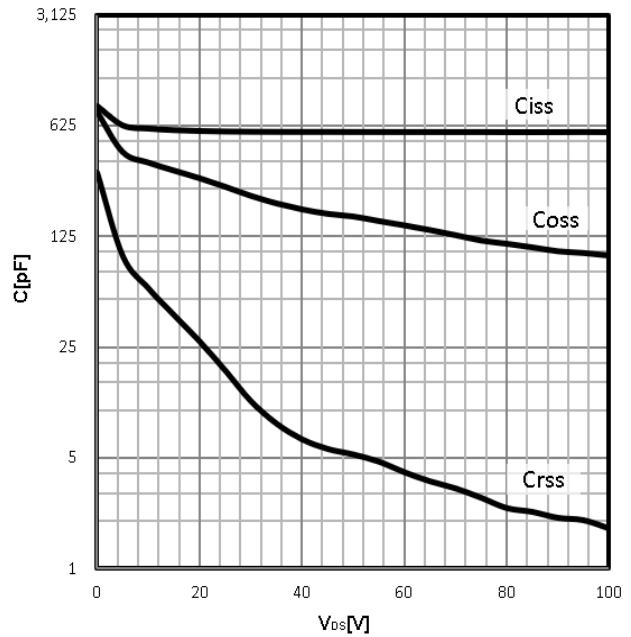
$$V_{BR(DSS)}=f(T_j); I_D=250\mu A$$


Typ. gate charge

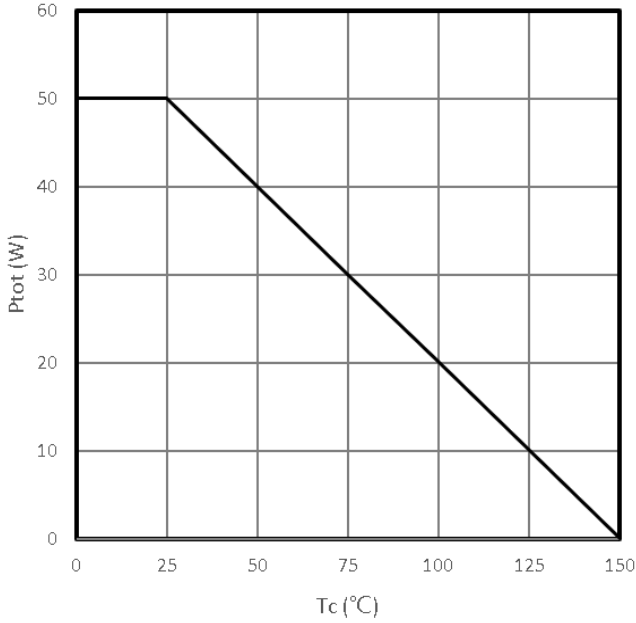
$$V_{GS}=f(Q_g); I_D=10A$$


Typ. capacitances

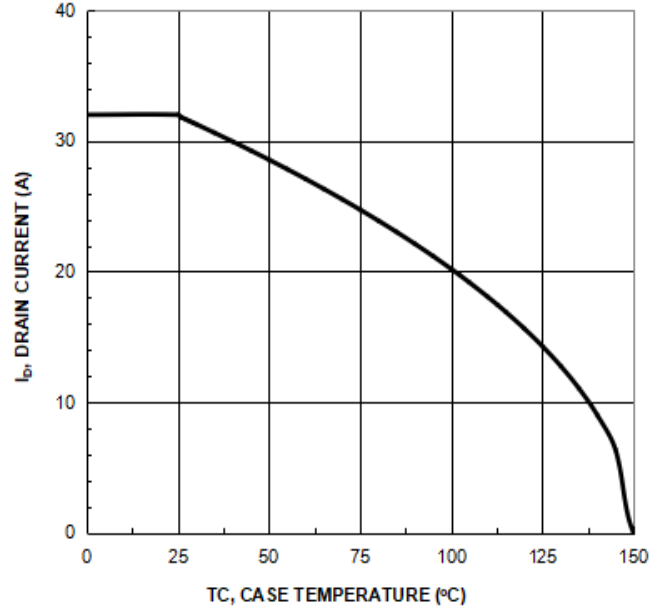
$$C=f(V_{DS}); V_{GS}=0V; f=1MHz$$



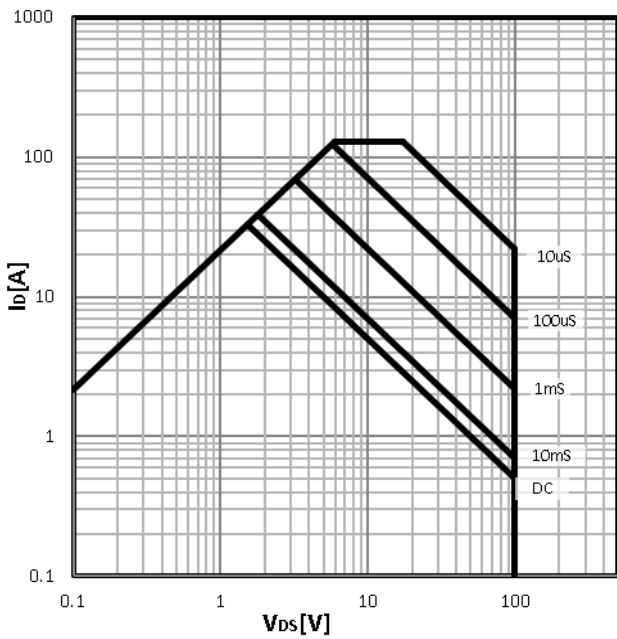
Power Dissipation
 $P_{tot}=f(T_C)$



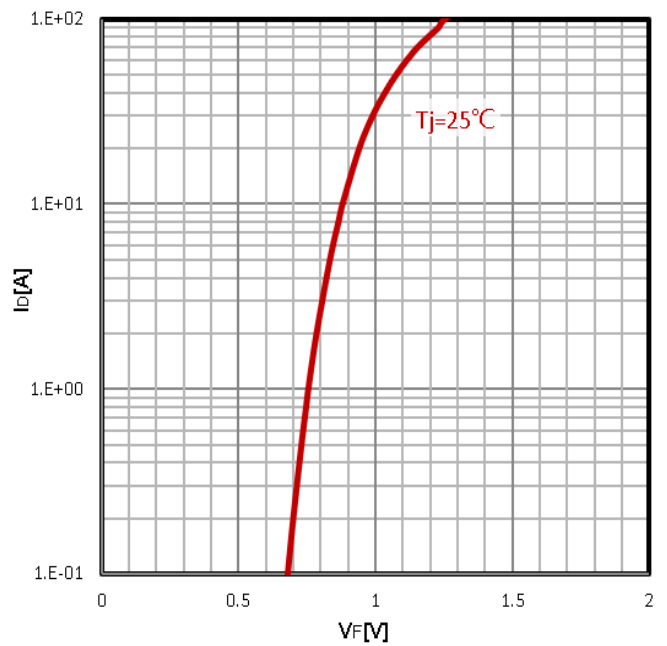
Maximum Drain Current
 $I_D=f(T_C)$



Safe operating area
 $I_D=f(V_{DS})$

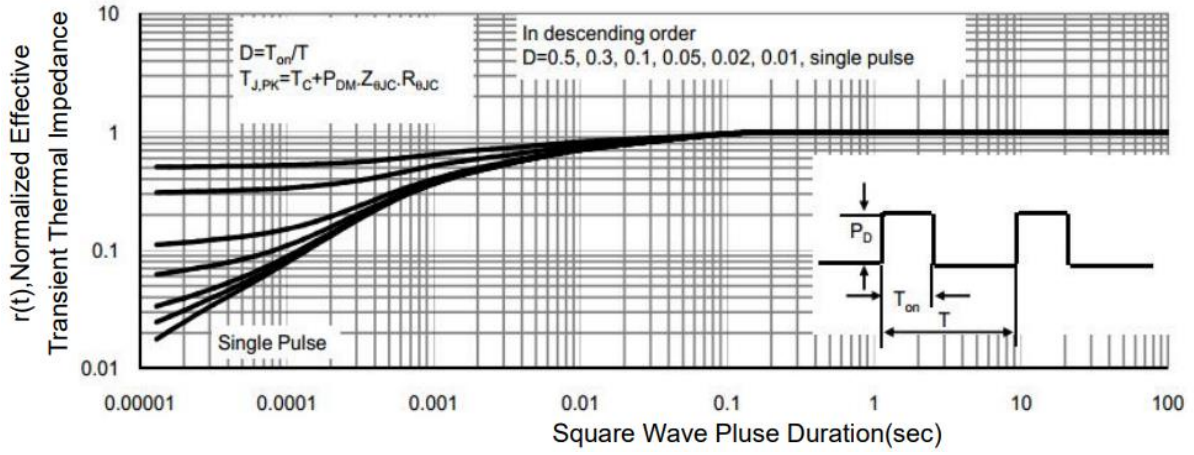


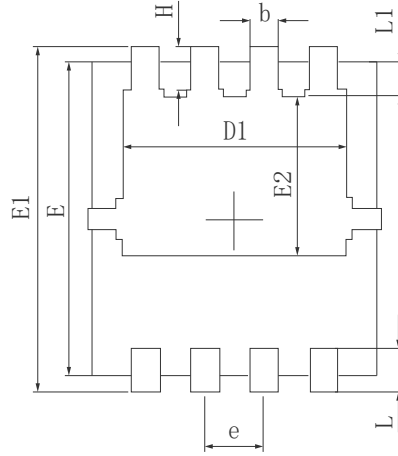
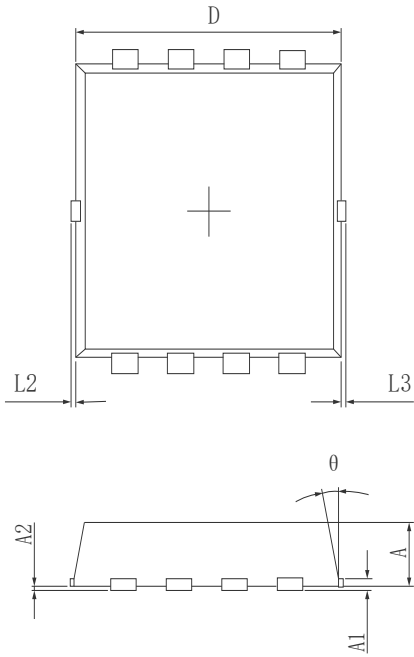
Body Diode Forward Voltage Variation
 $I_F=f(V_{GS})$



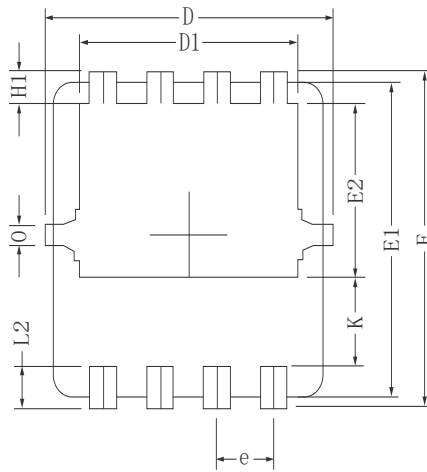
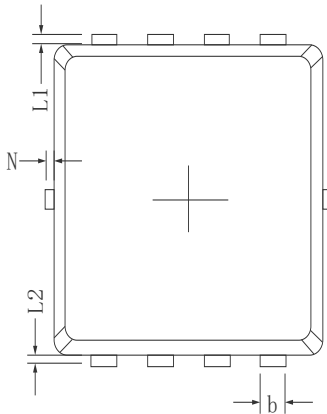
Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

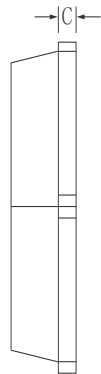
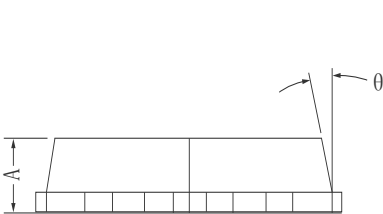


●Dimensions (PDFN3.3*3.3)


SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.700	0.800	0.900
A1	0.152REF.		
A2	0~0.05		
D	3.000	3.100	3.200
D1	2.300	2.450	2.600
E	2.900	3.000	3.100
E1	3.150	3.300	3.450
E2	1.320	1.520	1.720
b	0.200	0.300	0.400
e	0.550	0.650	0.750
L	0.300	0.400	0.500
L1	0.180	0.330	0.480
L2	0~0.100		
L3	0~0.100		
H	0.315	0.415	0.515
θ	8°	10°	12°

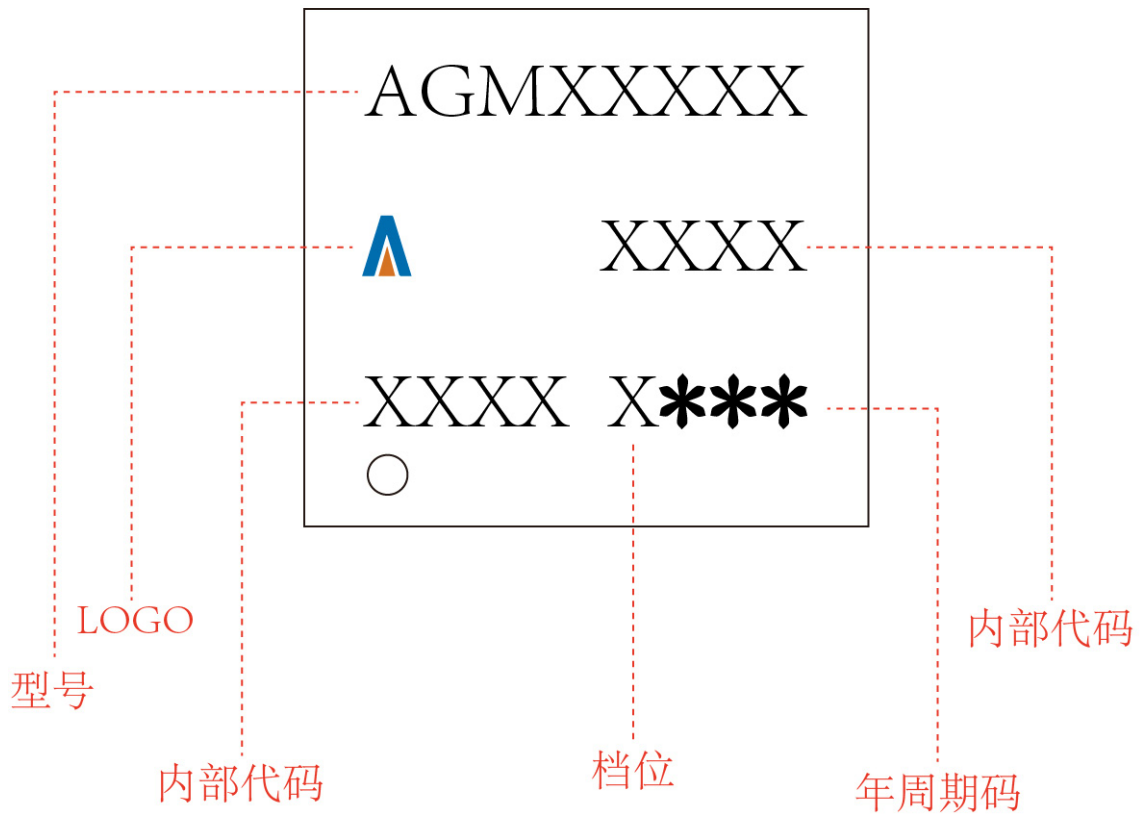


Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.65	0.75	0.85
b	0.25	0.30	0.35
C	0.15	0.20	0.25
D	3.00	3.10	3.20
D1	2.40	2.50	2.60
E	3.20	3.30	3.40
E1	3.00	3.10	3.20
E2	1.60	1.70	1.80
e	0.65 BSC.		
H1	0.21	0.31	0.41
H2	0.30	0.40	0.50
K	0.78	0.88	0.98
L1/L2	0.10 REF.		
θ	11°	12°	13°
N	0	-	0.15
0	0.2 REF.		



PDFN3.3*3.3

Marking Instructions:




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